Abstracts

L- and S-band Low-Noise Cryogenic GaAs FET Amplifiers (Short Papers)

S. De Panfilis and J. Rogers. "L- and S-band Low-Noise Cryogenic GaAs FET Amplifiers (Short Papers)." 1988 Transactions on Microwave Theory and Techniques 36.3 (Mar. 1988 [T-MTT]): 607-610.

We present the results of the construction and testing of three cryogenic low-noise GaAs FET amplifiers, based on a National Radio Astronomy Observatory design, to be used in a detector for the axion, a hypothetical particle. The amplifiers are centered on 1.1 GHz, 1.1 GHz, and 2.4 GHz, have a gain of approximately 30 dB in bandwidths of 300 MHz, 225 MHz, and 310 MHz, and have minimum noise temperatures of 7.8 K, 8 K, and 15 K, respectively.

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